Part Number	Customer

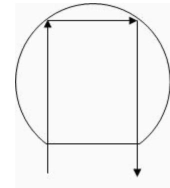
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	675.00 +/- 6.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	7.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100}+/-1 degree	Wafer Vendor
	13.0	Handle Thickness	505.00 +/- 5.00 µm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	10 ~ 20 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Lapped/etched with lasermark	Wafer Vendor
DeviceSilicon	18.0	Device Growth Method	FZ	Wafer Vendor
	19.0	Device Orientation	{100}+/-1 degree	Wafer Vendor
	20.0	Oxygen Concentration	<2.5 E16 atoms/cm3	Wafer Vendor
	21.0	Carbon Concentration	<3.0 E16 atoms/cm3	Wafer Vendor
	22.0	Nominal Thickness	170.00 +/- 1.00 µm	ADE single point 100%
	23.0	Distance to device silicon edge from wafer edge	<= 1 mm	Typical by Process
	24.0	Device Doping Type	P	Wafer Vendor
	25.0	Device Dopant	Boron	Wafer Vendor
	26.0	Device Resistivity	1000 ~ 3000 Ohm-cm	Wafer Vendor
	27.0	Voids	0	Bright Light, 100% (note 2)
	28.0	Scratches	total length < 5mm	Bright Light, 100% (note 2)
	29.0	Haze	none	Bright Light, 100% (note 2)
	30.0	LPD Count	<35 ppw @ 0.3um	LPD Particle Count Scan 100%

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

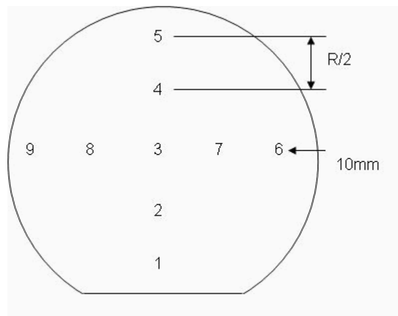
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information